

DMN26D0UDJ

DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}$	I_D $T_A = +25^\circ\text{C}$
20V	3.0Ω @ $V_{GS} = 4.5\text{V}$	240mA
	6.0Ω @ $V_{GS} = 1.8\text{V}$	180mA

Description

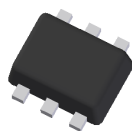
This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- DC-DC Converters
- Power management functions



SOT963



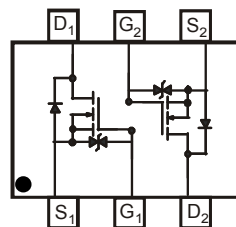
Top View

Features

- Dual N-Channel MOSFET
- Low On-Resistance:
 - 3.0Ω @ 4.5V
 - 4.0Ω @ 2.5V
 - 6.0Ω @ 1.8V
 - 10Ω @ 1.5V
- Very Low Gate Threshold Voltage, 1.05V max
- Low Input Capacitance
- Fast Switching Speed
- Ultra-Small Surface Mount Package
- ESD Protected Gate (HBM 300V)
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

Mechanical Data

- Case: SOT963
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.0027 grams (approximate)

Top View
Schematic and Transistor Diagram

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain Source Voltage			V_{DSS}	20	V
Gate-Source Voltage			V_{GSS}	± 10	V
Continuous Drain Current (Note 6) $V_{GS} = 4.5\text{V}$	Steady State	$T_A = +25^\circ\text{C}$	I_D	240	mA
		$T_A = +70^\circ\text{C}$		190	
Continuous Drain Current (Note 6) $V_{GS} = 1.8\text{V}$	Steady State	$T_A = +25^\circ\text{C}$	I_D	180	mA
		$T_A = +70^\circ\text{C}$		140	
Pulsed Drain Current - $T_P = 10\mu\text{s}$			I_{DM}	805	mA

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	P_D	300	mW
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	409	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	20	—	—	V	$V_{GS} = 0\text{V}, I_D = 100\mu\text{A}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	500	nA	$V_{DS} = 20\text{V}, V_{GS} = 0\text{V}$
@ $T_J = +85^\circ\text{C}$ (Note 8)				1.7	μA	$V_{DS} = 2.6\text{V}, V_{GS} = 0\text{V}$
Gate-Body Leakage	I_{GSS}	—	—	± 1 ± 100	μA nA	$V_{GS} = \pm 10\text{V}, V_{DS} = 0\text{V}$ $V_{GS} = \pm 5\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(th)}$	0.45	0.8	1.05	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(on)}$	—	1.8	3.0	Ω	$V_{GS} = 4.5\text{V}, I_D = 100\text{mA}$
		—	2.5	4.0		$V_{GS} = 2.5\text{V}, I_D = 50\text{mA}$
		—	3.4	6.0		$V_{GS} = 1.8\text{V}, I_D = 20\text{mA}$
		—	4.7	10.0		$V_{GS} = 1.5\text{V}, I_D = 10\text{mA}$
		—	9.5	—		$V_{GS} = 1.2\text{V}, I_D = 1\text{mA}$
Forward Transconductance	$ Y_{fs} $	180	240	—	mS	$V_{DS} = 10\text{V}, I_D = 0.1\text{A}$
Source-Drain Diode Forward Voltage	V_{SD}	0.5	0.8	1.0	V	$V_{GS} = 0\text{V}, I_S = 10\text{mA}$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	14.1	—	pF	$V_{DS} = 15\text{V}, V_{GS} = 0\text{V}$ $f = 1.0\text{MHz}$
Output Capacitance	C_{oss}	—	2.9	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	1.6	—	pF	
SWITCHING CHARACTERISTICS, $V_{GS} = 4.5\text{V}$ (Note 8)						
Turn-On Delay Time	$t_{d(on)}$	—	3.8	—	ns	$V_{GS} = 4.5\text{V}, V_{DD} = 10\text{V}$ $I_D = 200\text{mA}, R_G = 2.0\Omega$
Rise Time	t_r	—	7.9	—		
Turn-Off Delay Time	$t_{d(off)}$	—	13.4	—		
Fall Time	t_f	—	15.2	—		



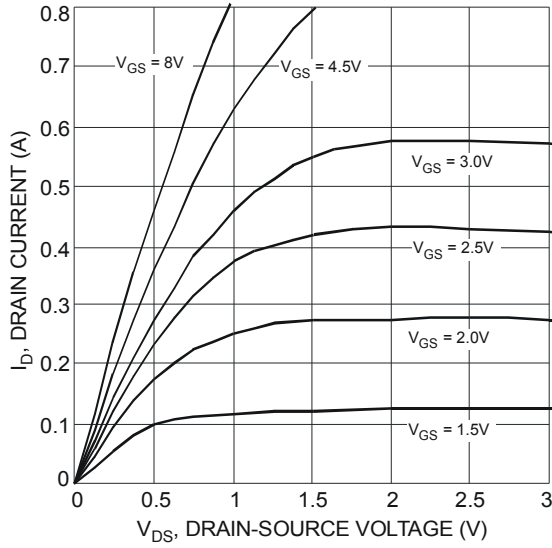


Fig. 1 Typical Output Characteristic

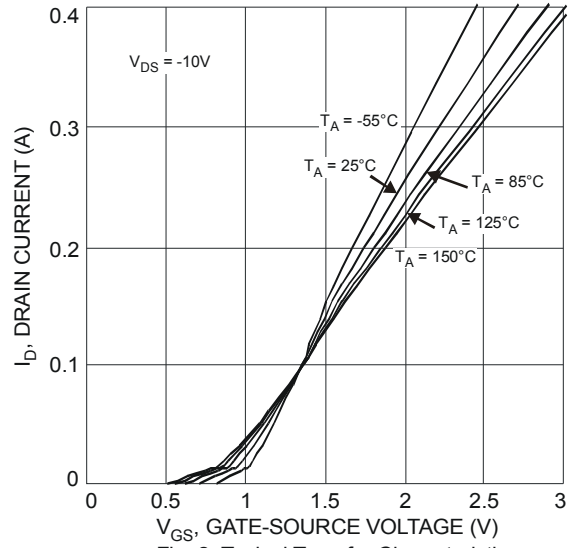


Fig. 2 Typical Transfer Characteristic

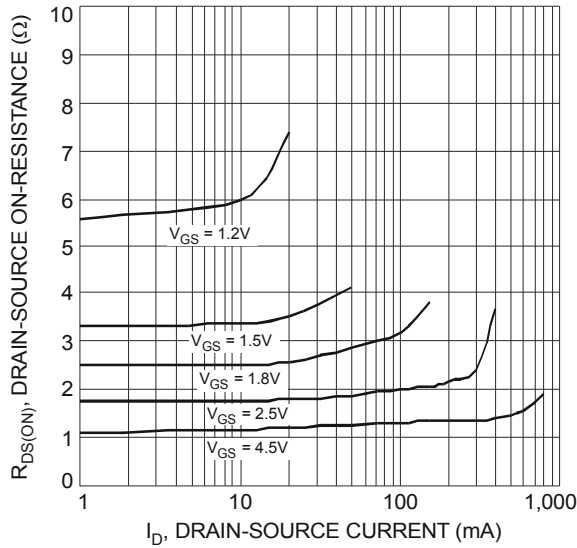


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

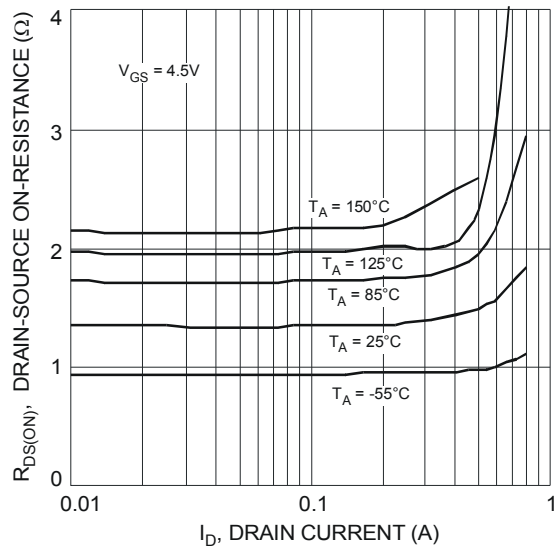


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

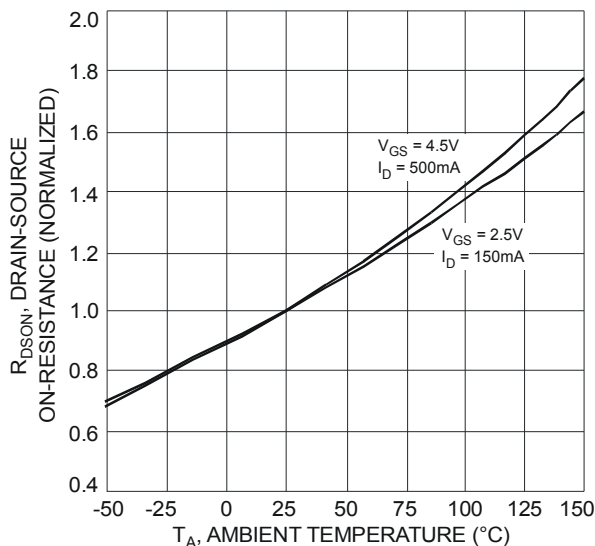


Fig. 5 On-Resistance Variation with Temperature

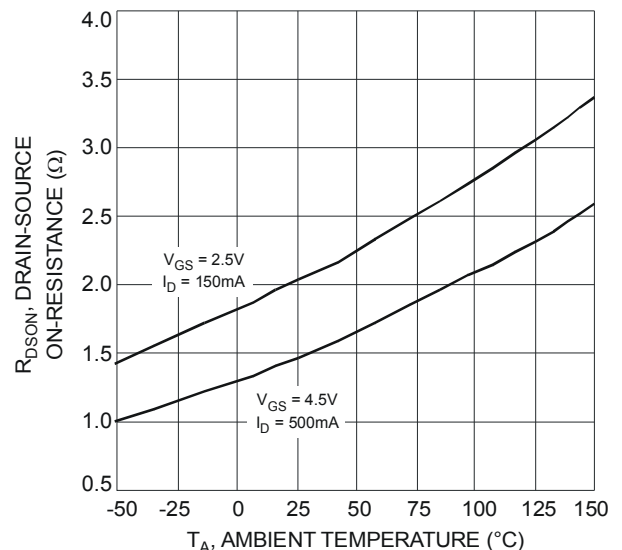


Fig. 6 On-Resistance Variation with Temperature



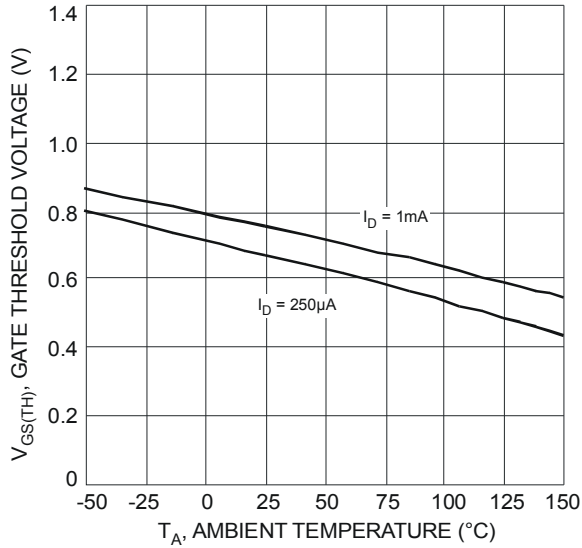


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

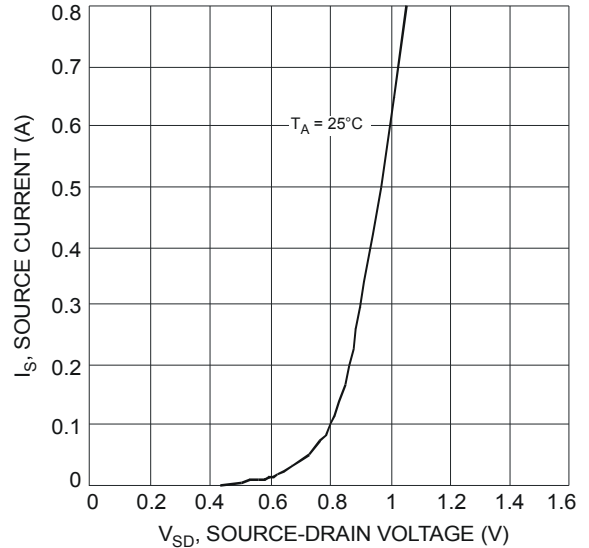


Fig. 8 Diode Forward Voltage vs. Current

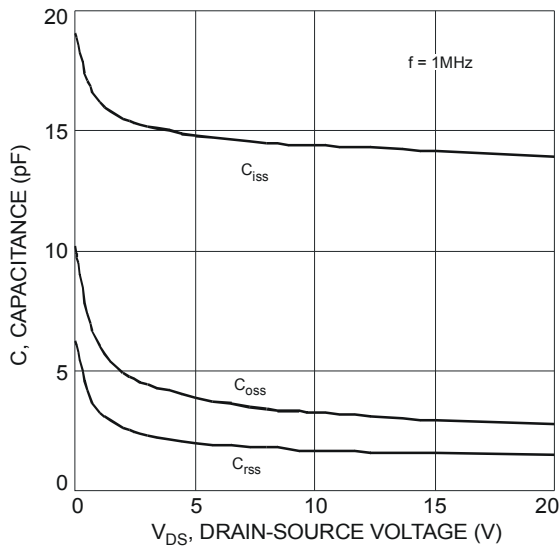


Fig. 9 Typical Total Capacitance

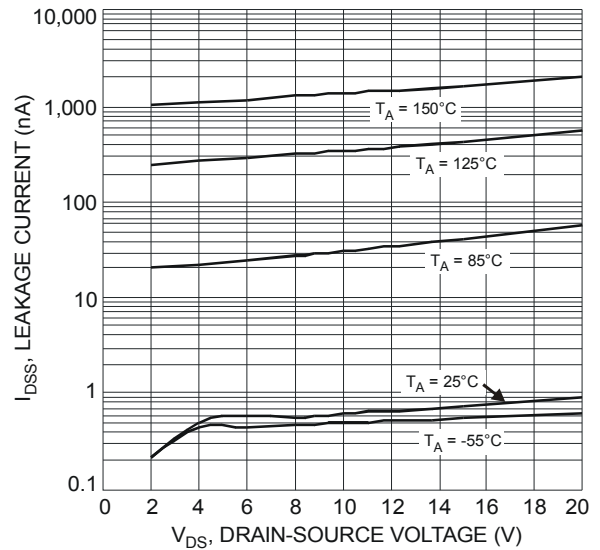
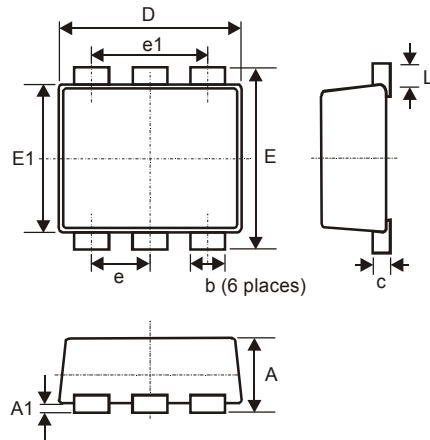


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

Package Outline Dimensions



SOT963			
Dim	Min	Max	Typ
A	0.40	0.50	0.45
A1	0	0.05	-
c	0.120	0.180	0.150
D	0.95	1.05	1.00
E	0.95	1.05	1.00
E1	0.75	0.85	0.80
L	0.05	0.15	0.10
b	0.10	0.20	0.15
e	0.35 Typ		
e1	0.70 Typ		
All Dimensions in mm			

